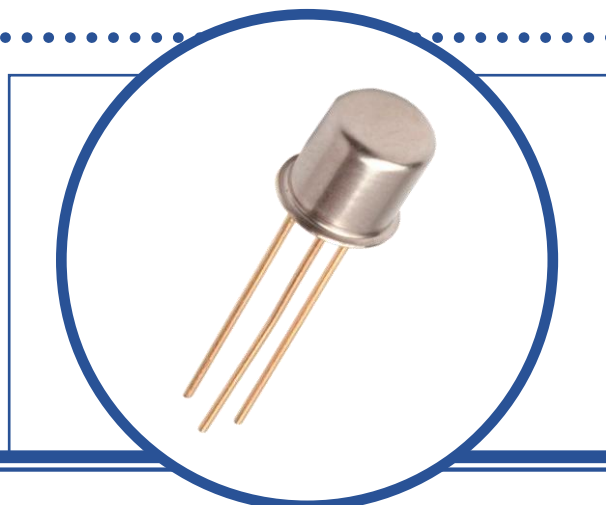


SILICON SMALL SIGNAL N-CHANNEL JFET

2N4392

- Hermetic TO18 Package.
- Low on Resistance
- Fast Switching
- Screening Options Available.



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

| | | |
|-----------|--|--------------------------------|
| V_{DS} | Drain – Source Voltage | 40V |
| V_{GS} | Gate – Source Voltage | -40V |
| V_{GD} | Gate – Drain Voltage | -40V |
| I_G | Gate Current | 50mA |
| P_D | Total Power Dissipation at $T_A = 25^\circ\text{C}$ Derate Above 25°C | 300mW 2mW/ $^\circ\text{C}$ |
| T_J | Junction Temperature Range | -65 to +175 $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -65 to +200 $^\circ\text{C}$ |

THERMAL PROPERTIES

| Symbols | Parameters | Max. | Units |
|-----------------|---|------|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction To Ambient | 500 | $^\circ\text{C/W}$ |

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



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SILICON SMALL SIGNAL N-CHANNEL JFET 2N4392

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

| Symbols | Parameters | Test Conditions | Min. | Typ. | Max. | Units |
|-----------------|---------------------------------|--|------|------|------|----------|
| $V_{(BR)GSS}$ | Gate – Source Breakdown Voltage | $V_{DS} = 0$ $I_G = 1.0\mu\text{A}$ | -40 | | | V |
| $V_{GS(off)}$ | Gate – Source Cut-off Voltage | $V_{DS} = 20\text{V}$ $I_D = 1.0\text{nA}$ | -2 | | -5 | |
| $I_{DSS}^{(1)}$ | Zero Gate Voltage Drain Current | $V_{DS} = 20\text{V}$ $V_{GS} = 0$ | 25 | | 75 | mA |
| I_{GSS} | Gate Reverse Current | $V_{DS} = 0$ $V_{GS} = -20\text{V}$ $T_A = 150^\circ\text{C}$ | | | -100 | pA |
| | | | | | -200 | nA |
| $I_{D(off)}$ | Drain Cut-off Current | $V_{DS} = 20\text{V}$ $V_{GS} = -7\text{V}$ $T_A = 150^\circ\text{C}$ | | | 100 | pA |
| | | | | | 200 | nA |
| $V_{DS(on)}$ | Drain – Source On Voltage | $V_{GS} = 0$ $I_D = 6\text{mA}$ | | | 0.4 | V |
| $R_{DS(on)}$ | Drain – Source On Resistance | $V_{GS} = 0$ $I_D = 1.0\text{mA}$ | | | 60 | Ω |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|--------------|--|---|--|--|----|----------|
| C_{iss} | Common – Source Input Capacitance | $V_{DS} = 20\text{V}$ $V_{GS} = 0$ $f = 1.0\text{MHz}$ | | | 26 | pF |
| C_{rss} | Common – Source Reverse Transfer Capacitance | $V_{DS} = 0$ $V_{GS} = -7\text{V}$ $f = 1.0\text{MHz}$ | | | 5 | |
| $R_{DS(on)}$ | Drain – Source On Resistance | $V_{GS} = 0$ $I_D = 0$ $f = 1.0\text{KHz}$ | | | 60 | Ω |
| t_r | Rise Time | $V_{DD} = 10\text{V}$ $V_{GSX} = -7\text{V}$ $V_{GS} = 0\text{V}$ $I_{D(on)} = 6\text{mA}$ | | | 5 | ns |
| $t_{d(on)}$ | Turn-on Delay Time | | | | 15 | |
| t_f | Fall Time | | | | 20 | |
| $t_{d(off)}$ | Turn-off Delay Time | | | | 35 | |

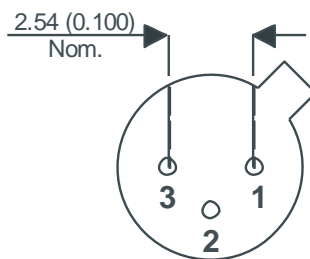
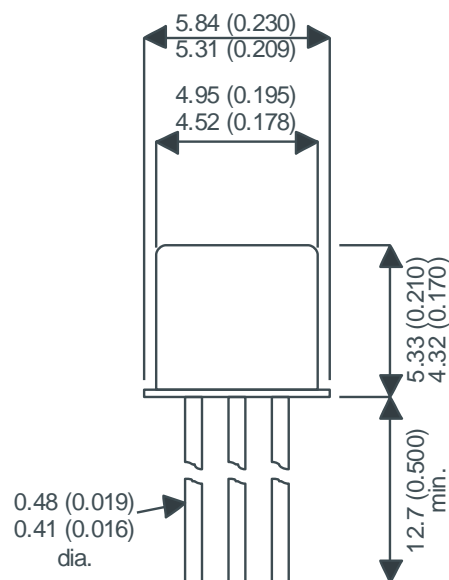
Notes

(1) Pulse Width $\leq 380\mu\text{s}$, $\delta \leq 2\%$

SILICON SMALL SIGNAL N-CHANNEL JFET 2N4392

MECHANICAL DATA

Dimensions in mm (inches)



TO-18 (TO-206AA) METAL PACKAGE Underside View

Pin 1 – Source

Pin 2 – Drain

Pin 3 - Gate